

2014 EUVL Workshop



EUVL Activities in China

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Activities only refer to published papers

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OUTLINE

- **Overview of EUVL in China**
 - ✓ National Research Foundation
 - ✓ Research Organization
- **2014 Activities Update**
 - ✓ Source
 - ✓ Mask
 - ✓ Optical Design
 - ✓ Multilayers
 - ✓ Metrology
 - ✓ Contamination Control
 - ✓ Simulation



National Research Foundation

- **NSFC:** National Natural Science Foundation of China.
- **NBRC:** National Basic Research Program of China.
- **NSTMP:** National Science and Technology Major Project.
- **MOE:** Ministry of Education



Research Organization

Chinese Academy of Sciences:



CIOMP



SIOM



IMECAS



AOE

...

Universities:



BIT

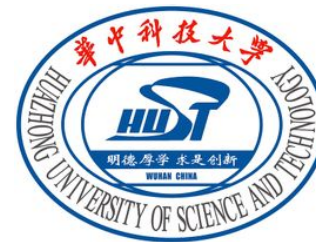


HIT



TJU

...



HUST



2014 Activities Update

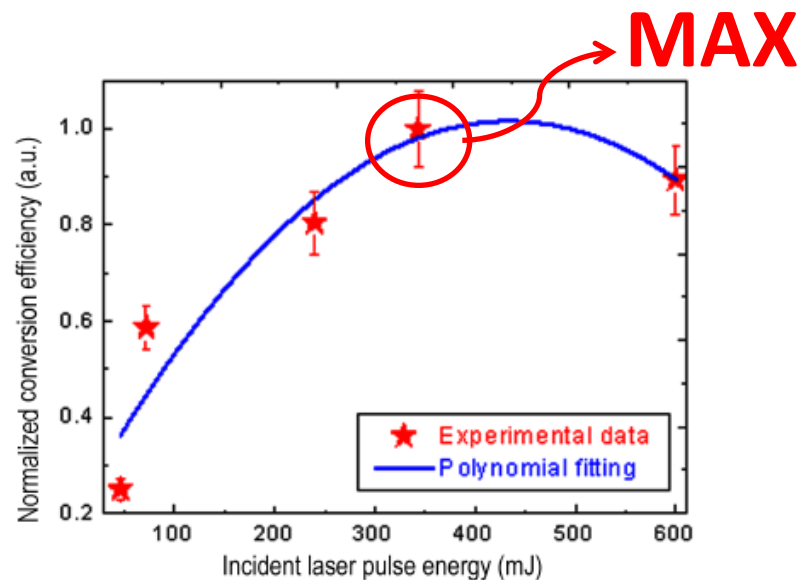
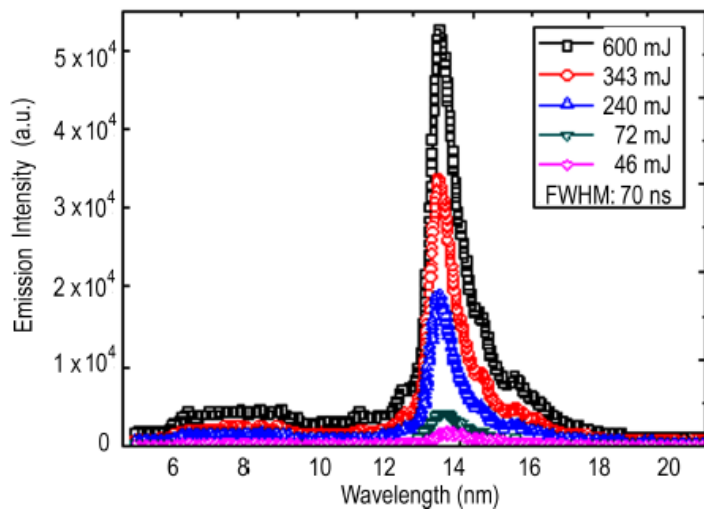
- ✓ **Source**
- ✓ **Mask**
- ✓ **Optical Design**
- ✓ **Multilayers**
- ✓ **Metrology**
- ✓ **Contamination Control**
- ✓ **Simulation**



2014 Activities Update

1. Source (Basic Research)

Spectral Efficiency of EUV Emission from CO₂ Laser-Produced Tin Plasma



Activities in Huazhong University of Science and Tech

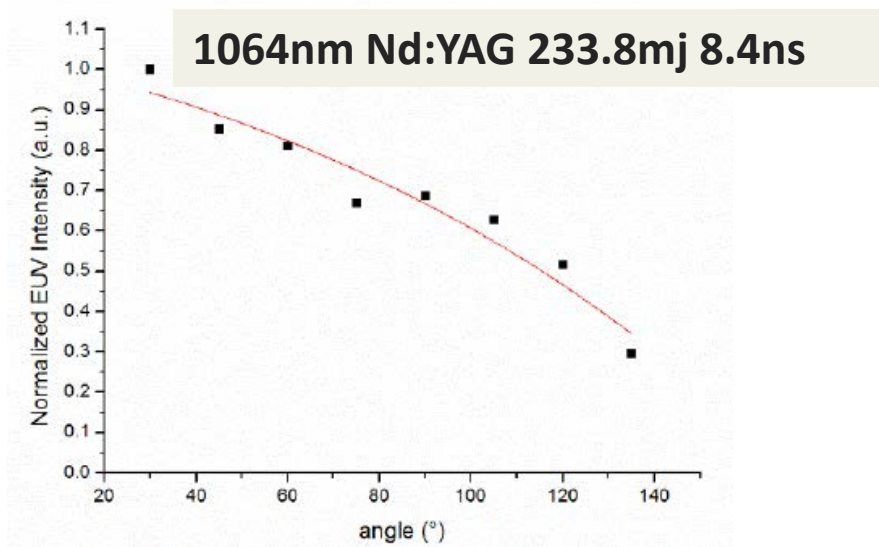
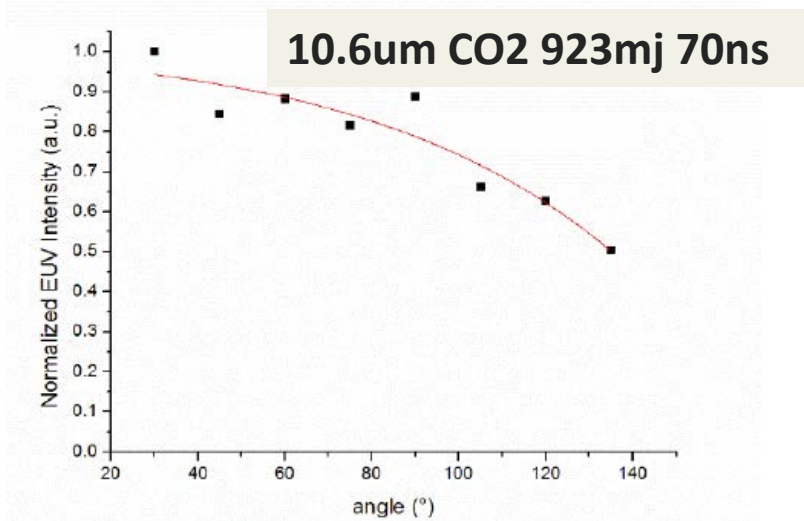
Ref. Plasma Science and Technology, 2013

Supported by NSFC...



2014 Activities Update

Emission properties of Tin droplets LPP sources



Activities in Huazhong University of Science and Tech

Ref.Proc.SPIE 90481V, 2014

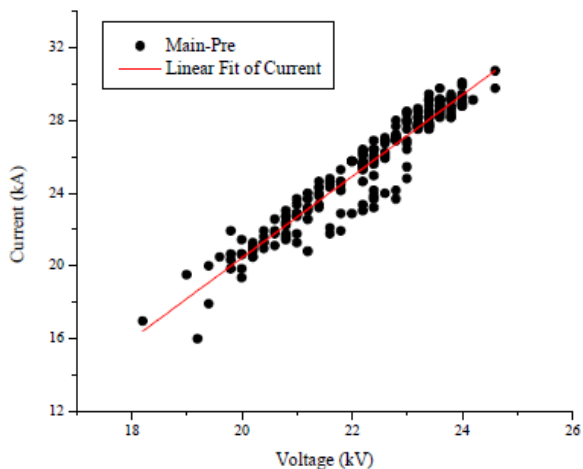
Supported by NSFC & NSTMP



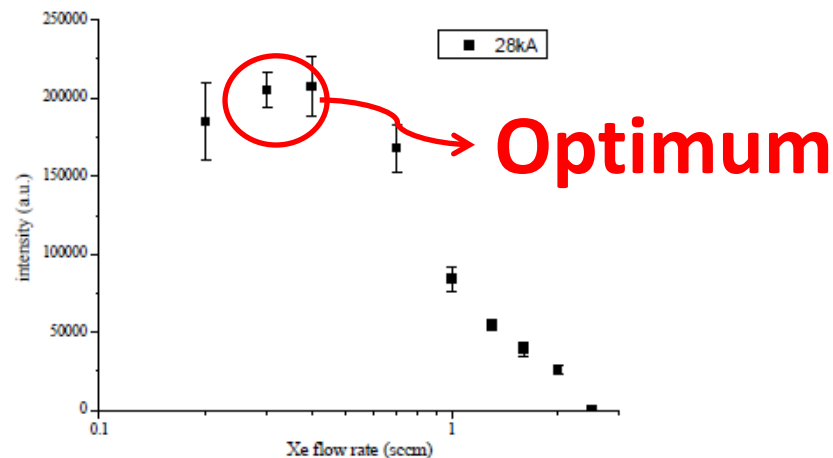
2014 Activities Update

Influence of Pre-pulse Power on Xe Capillary Discharge EUV Source

main-voltage and the current when discharging by the main-pre-pulse



13.5nm (2% bandwidth) emission and the flow rate of Xe



Activities in Harbin Institute of Technology (HIT)

“Ref. Plasma Science and Technology, 2013

Supported by NSFC&NSTMP



2014 Activities Update

Activities in SIOM

“Modulation of the Langmuir Oscillation on the plasma radiation by Rabi oscillation ”

Ref. [EUVL workshop, 2014](#)

“EUV Radiation Characteristics of Xe Cluster Ensemble Irradiated by Nanosecond and Femtosecond Lasers ”

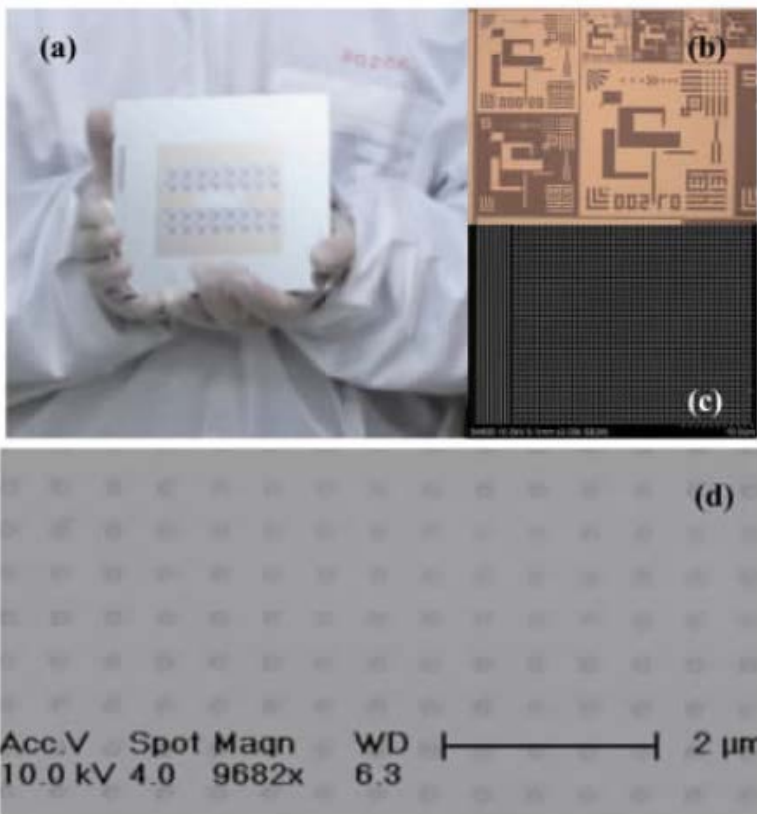
Ref. [EUVL workshop, 2014](#)



2014 Activities Update

2. Mask

Integrated Development of EUVL Mask at 32nm node



Mask CD < 100 nm
Mask CD Accuracy < 20 nm

Activities in IMCAS

Ref. Acta. Optica Sinica, 2013

Supported by NSFC

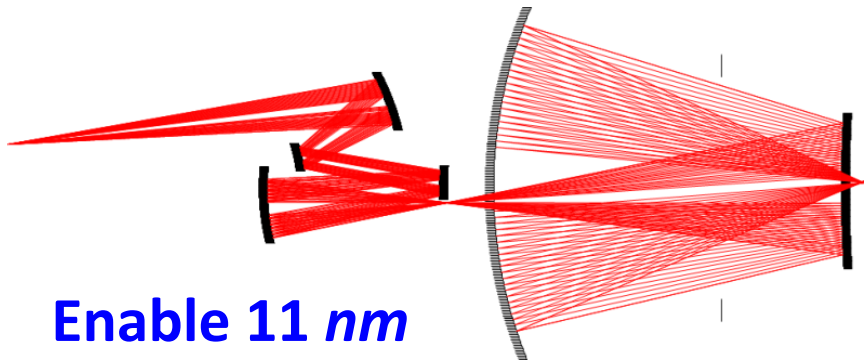


2014 Update (Basic Research)

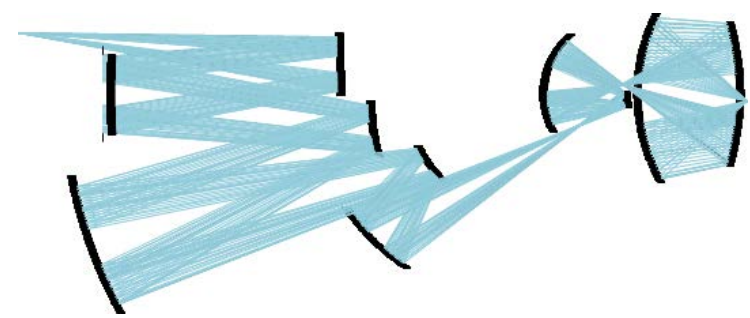
3. Optical Design (New Requirements)

Design of High-NA Projection Objective

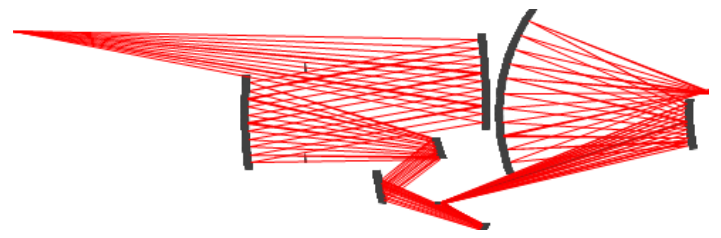
6M obscured objective NA0.5



10M obscured objective NA0.75



8M unobscured objective NA0.45



Activities in Beijing Institute of Technology (BIT)

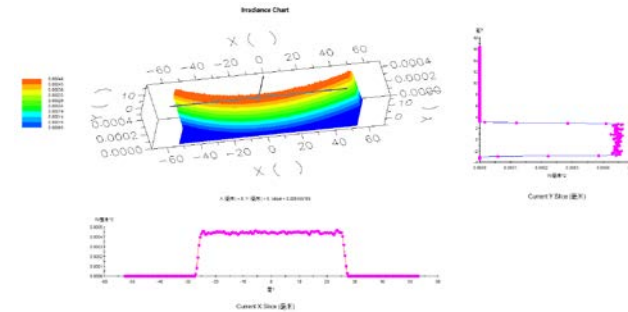
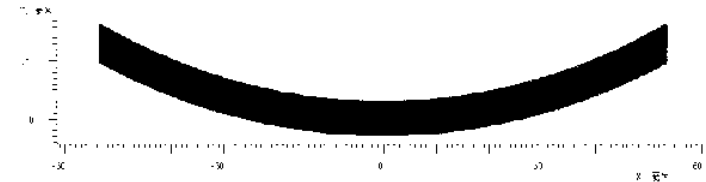
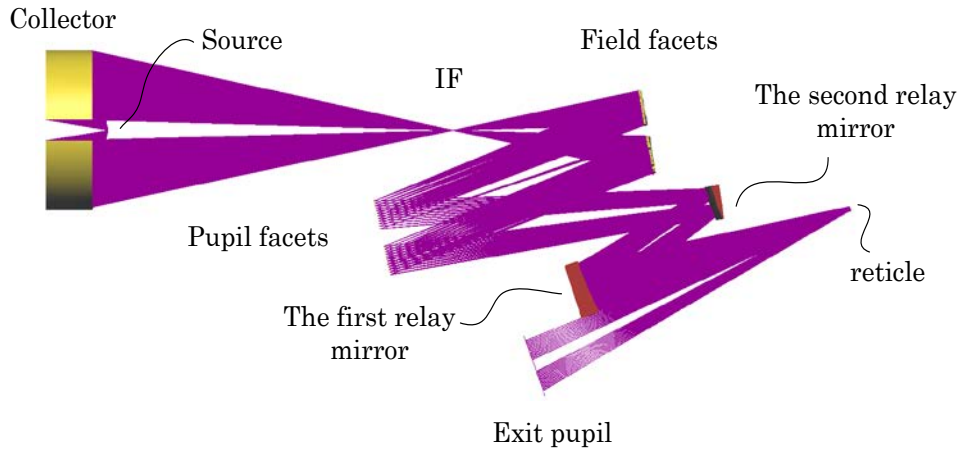
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Ref. Proc. SPIE 90482F 2014, Appl. Opt. 52(29) 2014 ,EUVL workshop 2014



2014 Update (Basic Research)

Design of EUV illuminator



	90-degree dipole illumination	45-degree quadrupole illumination	annular illumination
Pupil facets			
Exit pupil			

Illumination uniformity is better than 2.5%. Submitted to Appl. Opt.

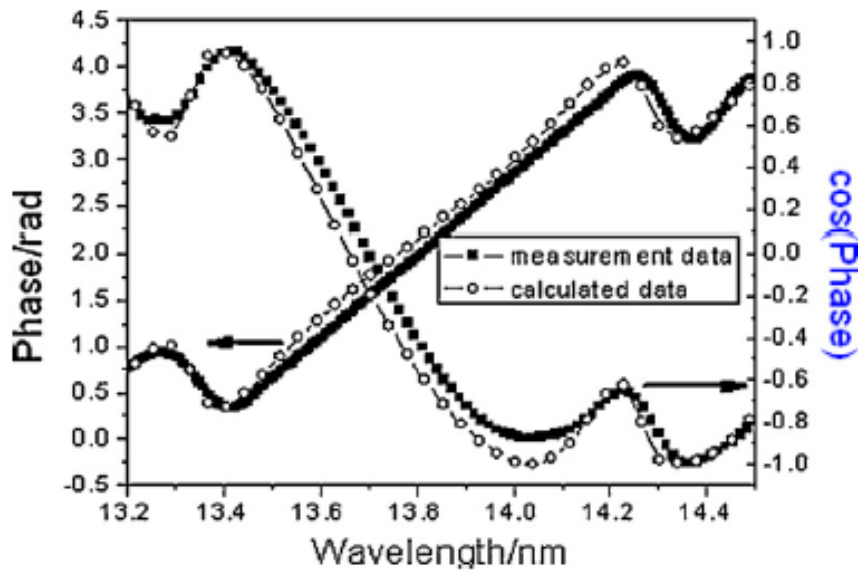
**Activities in (BIT)
Supported by
NSTMP & MOE**



2014 Update (Basic Research)

4. Multilayers (Basic Research)

“Reflective phase shift measurement of the Mo/Si multilayer mirror in extreme ultraviolet region”



Activities in Tongji University

Supported by NSFC, NSTMP...

Ref. Optik 124 (2013) 5003-5006

This work gives the chance to characterize the phase shift of the EUV multilayer mirrors for EUVL.



2014 Activities Update

Activities in CIOMP

“A Novel Model for Coated System Analysis in Extreme Ultra-Violet Lithography ”

Ref. [EUVL workshop, 2014](#)

Activities in SIOM

“Simplified Model for Spectrum Simulation of Multilayer with Buried Defect in EUV Lithography ”

Ref. [EUVL workshop, 2014](#)



2014 Activities Update

5. Metrology

Activities in (BIT)

Wavefront Metrology

Design of PS/PDI system for } Visible
EUV

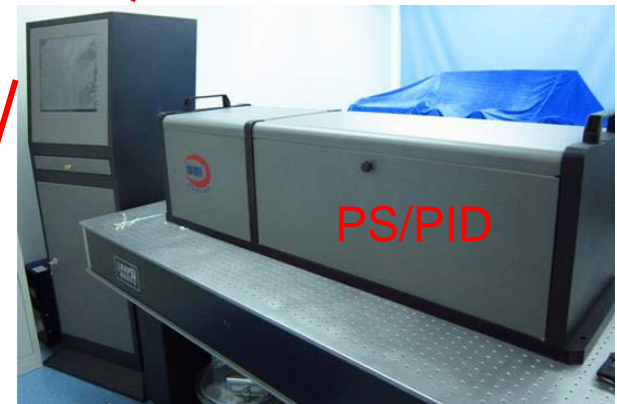
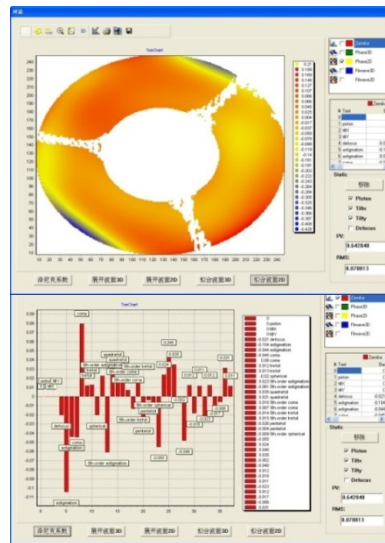
PS/PDI system @632.8nm has completed!

- Absolute accuracy 5 nm rms
- Repeatability 0.55 nm rms

Supported by NSTMP & MOE

New progress

- Measurement objectives with different NA (0.2 ~ 0.4)
- Automatic calibration and measurement



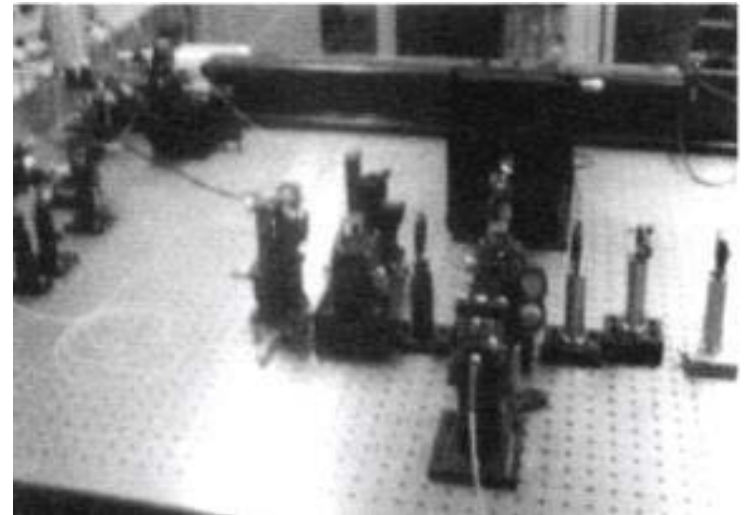
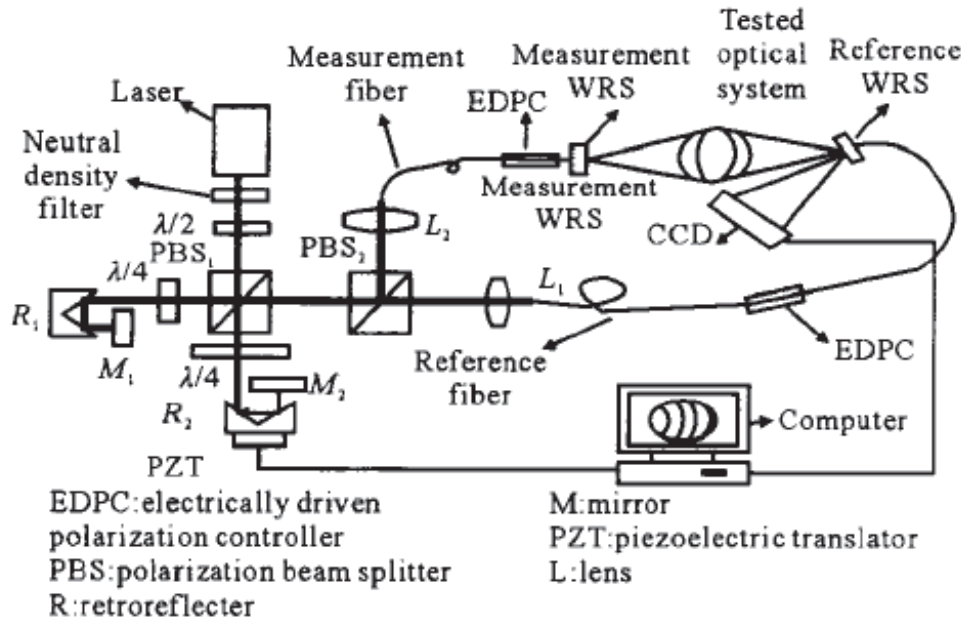


2014 Activities Update

Activities in CIOMP

Visible PS/PDI Repeatability improved.

Repeatability: $1/4000 \lambda$ rms ($\lambda=632.8\text{nm}$)



Ref. Infrared and Laser Engineering, Chinese Journal of Lasers, 28(2012).



2014 Activities Update

Activities in Institute of Optics and Electronics

“Calibration of the system error in pinhole diffracted interferometer”

PDI System error 0.009λ ($\lambda=632.8\text{nm}$)

Ref. Acta. Optica Sinica, 2013

Activities in SIOM

“Aberration measurement technique based on an analytical linear model of a through-focus aerial image”

Ref. Optics express, 2014

Lens aberration offset with an accuracy of 0.7 nm.

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2014 Activities Update

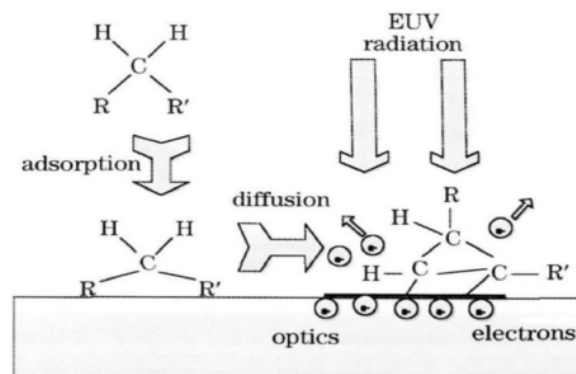
6. Contamination Control

Activities in CIOMP

“Carbon Contamination Modeling on Extreme Ultraviolet Optic Surface” Ref. Acta. Optica Sinica, 2013

“Simulation Model of Surface Carbon Deposition Contamination Under Extreme Ultraviolet Radiation” Ref. Acta. Optica Sinica, 2014

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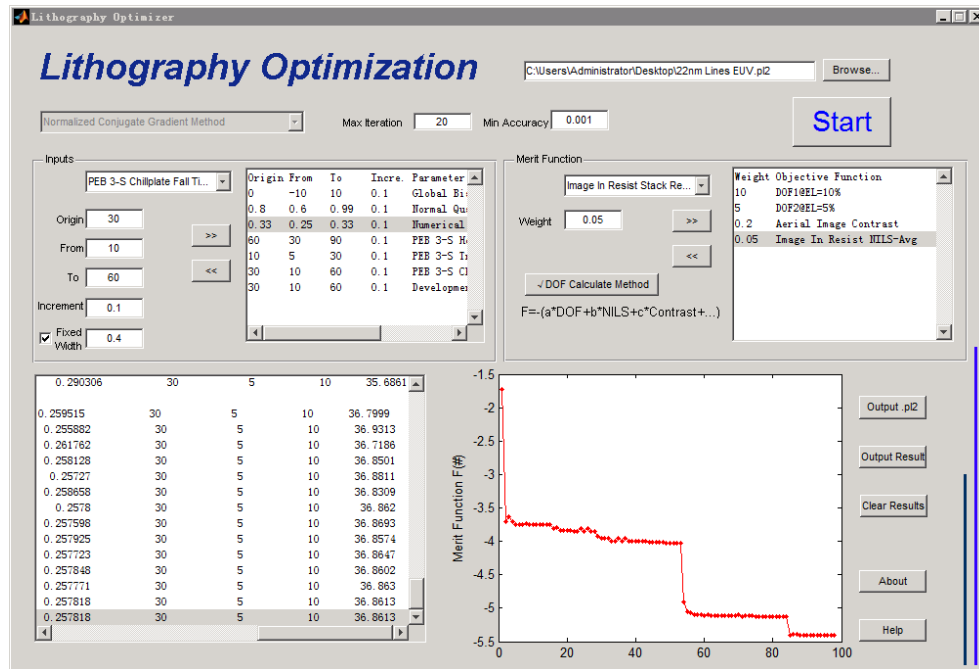




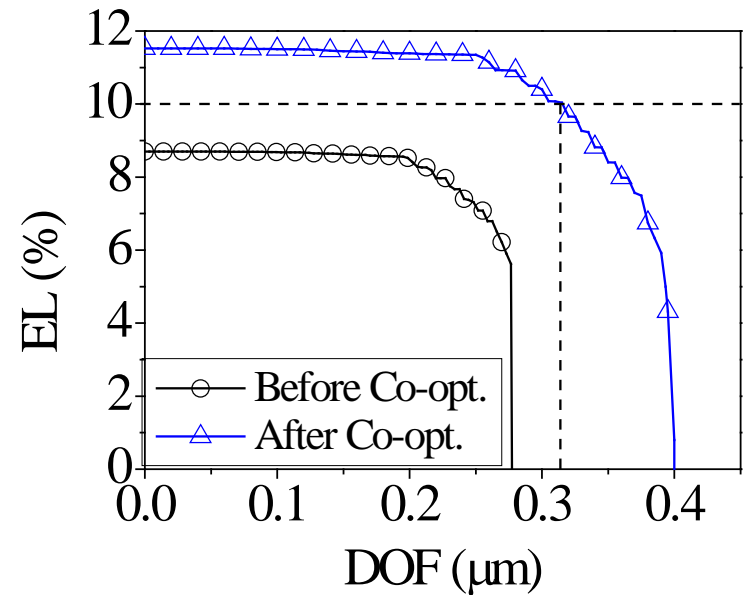
2014 Update (Basic Research)

7. Simulation

Co-optimize the EUV Litho-tool, Process, and Mask to improve the pattern fidelity and the process window



22 nm L/S=1:1



Activities in (BIT)

Supported by NSTMP



Abbreviations for Research Organization

AOE	Academy of Opto-electronics
SIOM	Shanghai Institute of Optics and Fine Mechanics
CIOMP	Changchun Institute of Optics, Fine Mechanics and Physics
IMECAS	Institute of Microelectronics
BIT	Beijing Institute of Technology
HIT	Harbin Institute of Technology
TJU	Tongji University
HUST	Huazhong University of Science and Technology



**More activities will be shown in
the future!**

Thank you for your attention !